

SANYO	No.512F	2SB698/2SD734
		PNP/NPN Epitaxial Planar Silicon Transistors 1W AF Output, Electronic Governor, DC-DC Converter Applications

() : 2SB698 for audio 1W output.

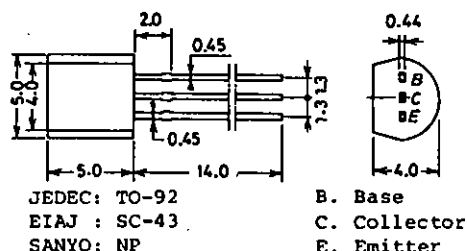
Absolute Maximum Ratings at $T_a=25^\circ\text{C}$		unit
Collector to Base Voltage	V_{CB0}	(-)25 V
Collector to Emitter Voltage	V_{CE0}	(-)20 V
Emitter to Base Voltage	V_{EB0}	(-)5 V
Collector Current	I_C	(-)0.7 A
Collector Current(Pulse)	I_{CP}	(-)1.5 A
Collector Dissipation	P_C	0.6 W
Junction Temperature	T_j	150 $^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150 $^\circ\text{C}$

Electrical Characteristics at $T_a=25^\circ\text{C}$		min	typ	max	unit
Collector Cutoff Current	I_{CBO} $V_{CB}=(-)20\text{V}, I_E=0$			(-)1.0	μA
Emitter Cutoff Current	I_{EBO} $V_{EB}=(-)4\text{V}, I_C=0$			(-)1.0	μA
DC Current Gain	$h_{FE(1)}$ $V_{CE}=(-)2\text{V}, I_C=(-)50\text{mA}$	60*		560*	
	$h_{FE(2)}$ $V_{CE}=(-)2\text{V}, I_C=(-)500\text{mA}$	50			
Gain-Bandwidth Product	f_T $V_{CE}=(-)10\text{V}, I_C=(-)50\text{mA}$		250		MHz
Output Capacitance	c_{ob} $V_{CB}=(-)10\text{V}, f=1\text{MHz}$		(13)		pF
C-E Saturation Voltage	$V_{CE(sat)}$ $I_C=(-)500\text{mA}, I_B=(-)50\text{mA}$		0.2	(-0.45)	V
B-E Saturation Voltage	$V_{BE(sat)}$ $I_C=(-)500\text{mA}, I_B=50\text{mA}$		(-)0.9		V
C-B Saturation Voltage	$V_{(BR)CBO}$ $I_C=(-)10\mu\text{A}, I_E=0$	(-)25			V
C-E Breakdown Voltage	$V_{(BR)CEO}$ $I_C=(-)1\text{mA}, R_{BE}=\infty$	(-)20			V
E-B Breakdown Voltage	$V_{(BR)EBO}$ $I_C=(-)10\mu\text{A}, I_C=0$	(-)5			V

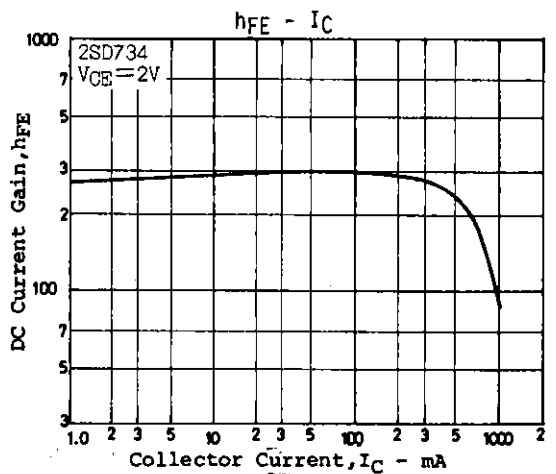
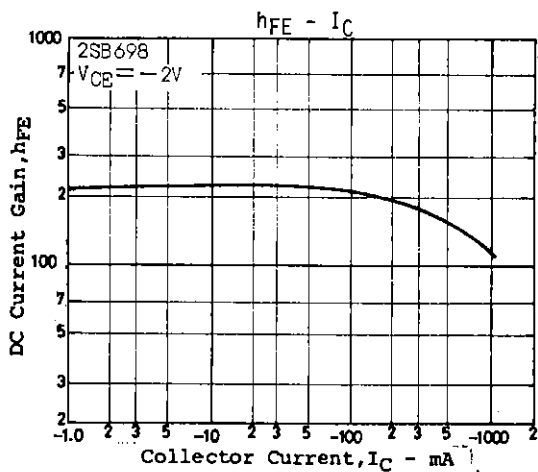
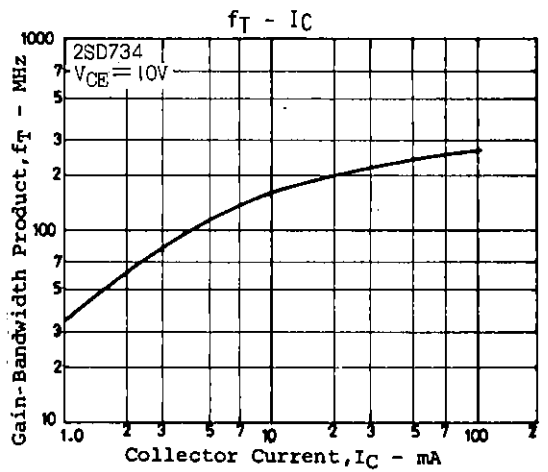
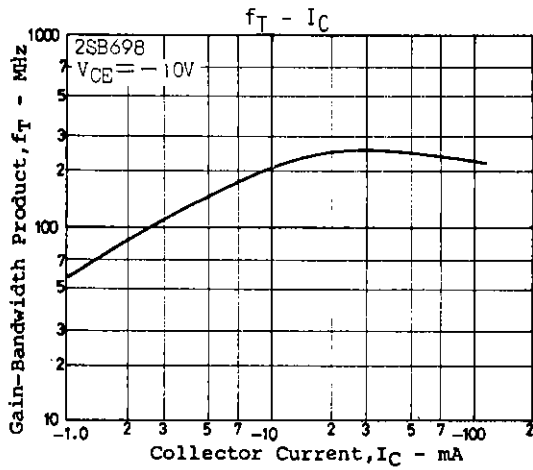
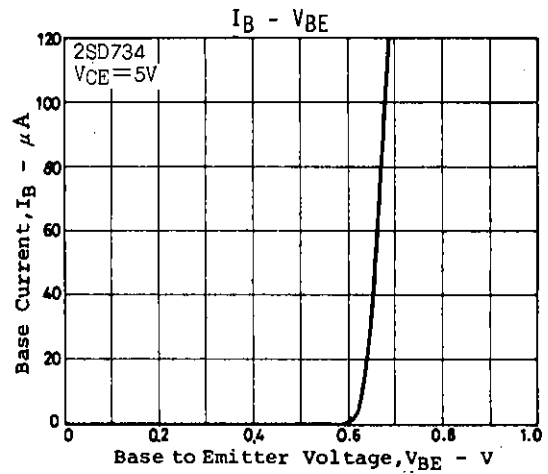
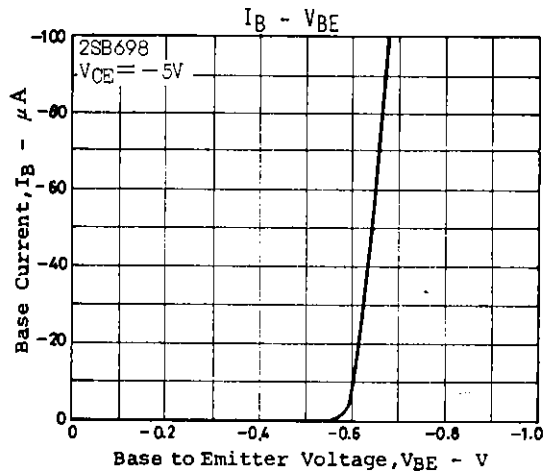
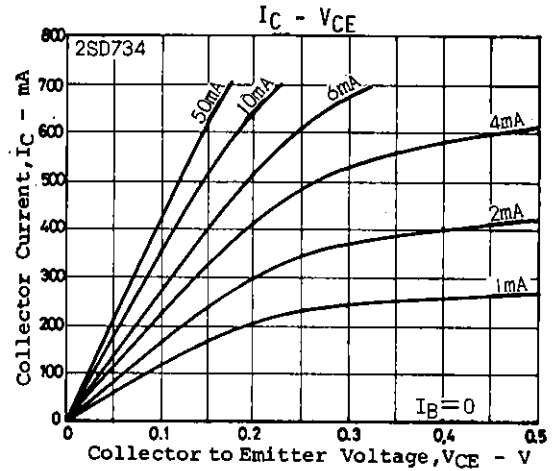
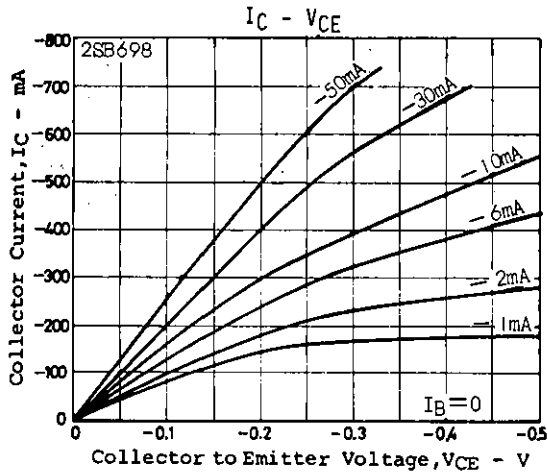
*: 2SB698/2SD734 are classified by 50mA h_{FE} as follows:

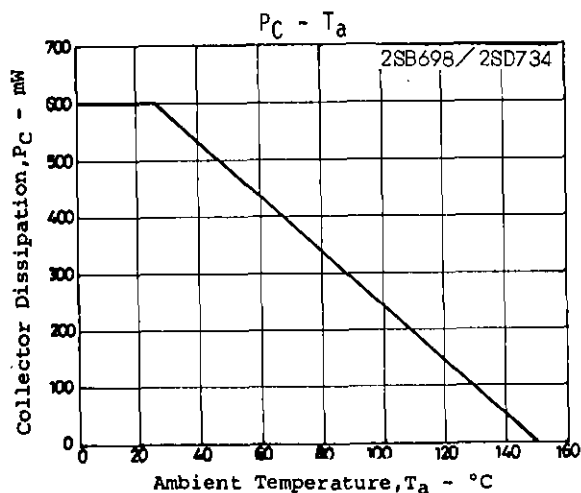
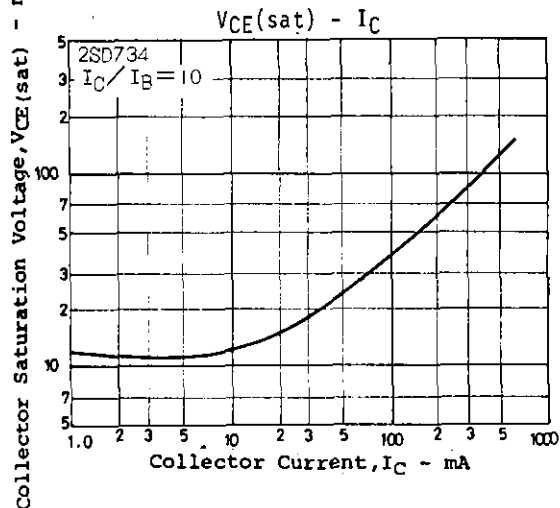
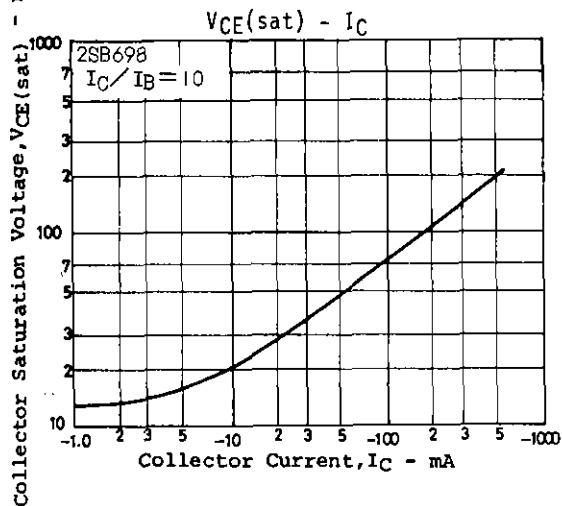
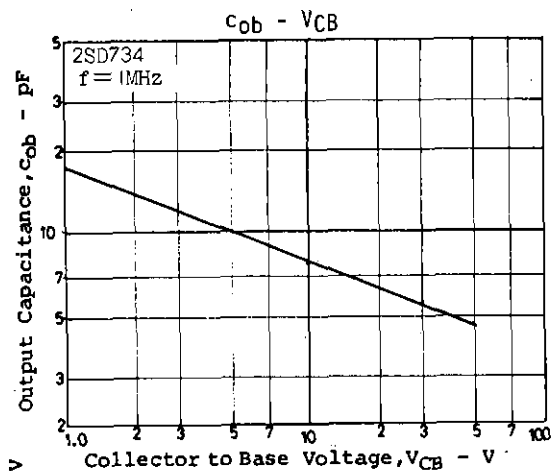
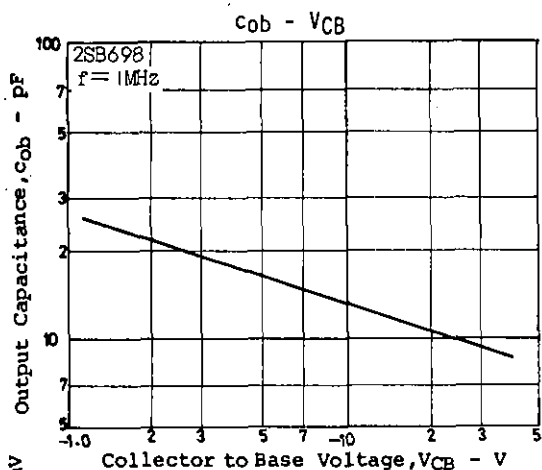
60	D	120	100	E	200	160	F	320	280	G	560
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Package Dimensions 2003A
(unit: mm)



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